

MICRO ELECTRONICS

2N3962

PNP
SILICON
TRANSISTOR

DESCRIPTION

2N3962 is PNP silicon planar transistor designed for AF small signal amplifier stages.

TO-18



CBE

ABSOLUTE MAXIMUM RATINGS

Collector-Emitter Voltage	V _{CEO}	60V
Collector-Base Voltage	V _{CBO}	60V
Emitter-Base Voltage	V _{EB0}	6V
Collector Current	I _C	200mA
Continuous Power Dissipation	P _d	360mW
Operating & Storage Junction Temperature	T _j , T _{stg}	-55 to +150°C

ELECTRO-OPTICAL CHARACTERISTICS

(T_a = 25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS
Collector-Emitter Breakdown Voltage	LV _{CEO}	60		V	I _C = 5mA, I _B = 0
Collector-Base Breakdown Voltage	BV _{CBO}	60		V	I _C = 10μA, I _E = 0
Emitter-Base Breakdown Voltage	BV _{EBO}	6		V	I _E = 10μA, I _C = 0
Collector Cutoff Current	I _{CES}		10	nA	V _{CE} = 50V, V _{EB} = 0
Emitter Cutoff Current	I _{EBO}		10	nA	V _{EB} = 4V, I _C = 0
D.C. Current Gain	H _{FE}	60			I _C = 0.001mA, V _{CE} = 5V
		100	300		I _C = 0.01mA, V _{CE} = 5V
		100	450		I _C = 1mA, V _{CE} = 5V
		90			I _C = 50mA, V _{CE} = 5V
Collector-Emitter Saturation Voltage	V _{CE(sat)}		0.25	V	I _C = 10mA, I _B = 0.5mA
			0.4	V	I _C = 50mA, I _B = 5mA
Base-Emitter Saturation Voltage	V _{BE(sat)}		0.95	V	I _C = 50mA, I _B = 5mA
Output Capacitance	C _{ob}		6	pF	V _{CB} = 10V, f = 1MHz
Noise Figure	N _F		3	dB	I _C = 0.02mA, V _{CE} = 5V R _{EB} = 10Kohm, f = 1kHz

* Pulse test : pulse width < 300μS, duty cycle < 2%.



MICRO ELECTRONICS LTD.

38, Hung To Road, Microtron Bldg, Kwun Tong, Kowloon, Hong Kong.

Kwun Tong P.O. Box 69477 Hong Kong. Fax No. 2341 0321 Telex: 43510 Micro Hx. Tel: 2343 0181-5

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